

INTERDIGITATED CAPACITOR AND METHOD OF MANUFACTURING THEREOF

ABSTRACT OF THE DISCLOSURE

The present invention provides a method of manufacturing an interdigitated semiconductor device. In one embodiment, the method comprises simultaneously forming first electrodes adjacent each other on a substrate, forming a dielectric layer between the first electrodes, and creating a second electrode between the first electrodes, the second electrode contacting the dielectric layer between the first electrodes to thereby form adjacent interdigitated electrodes. An interdigitated capacitor and a method of manufacturing an integrated circuit having an interdigitated capacitor are also disclosed.